

/ Descriptions

VRS0; Q Sr z hu Wuhqfk P RV
Dual N-Channel Power Trench MOSFET in a SOP-8 Plastic Package.

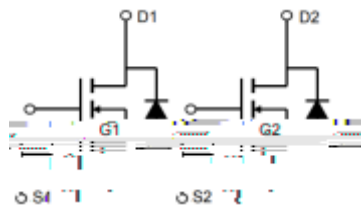
/ Features

$V_{DS}(V)=40V$ $I_D=8A$
 $R_{DS(ON)}@10V<20m\Omega$ (Typ. 22m Ω)
 $R_{DS(ON)}@4.5V<29.5m\Omega$ (Typ. 36m Ω)
HF Product.

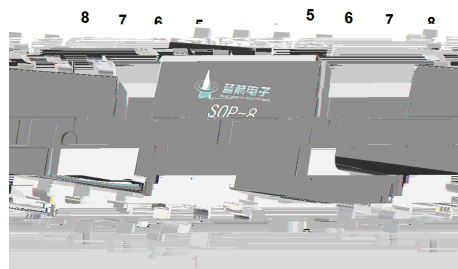
/ Applications

Battery protection, Load Switch, Power management.

/ Equivalent Circuit



/ Pinning



PIN1	S1	PIN 2	G1	PIN 3	S2	PIN 4	G2
PIN 5	D2	PIN 6	D2	PIN 7	D1	PIN 8	D1

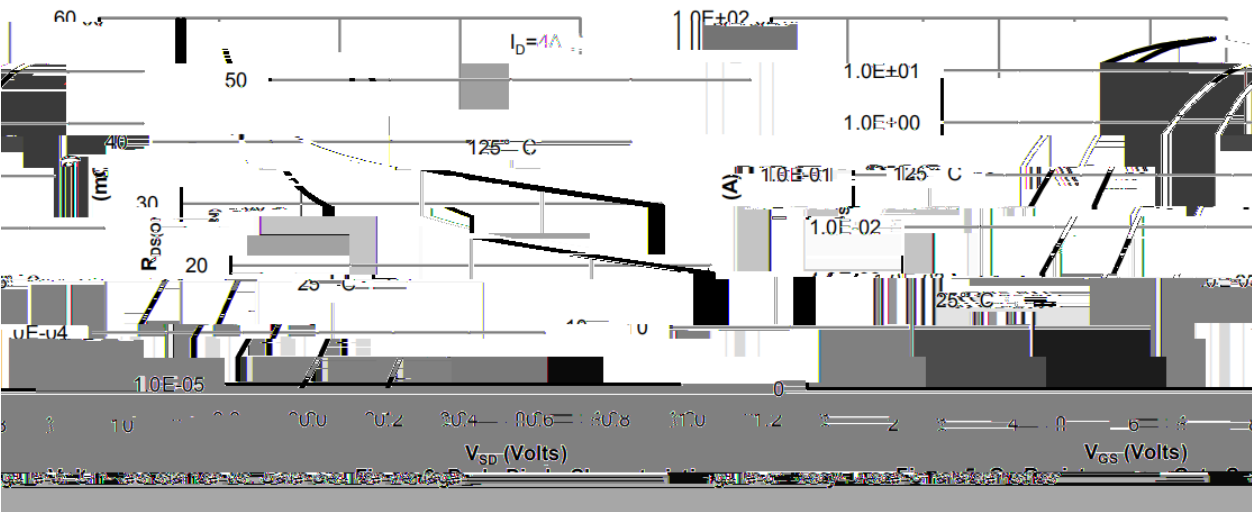
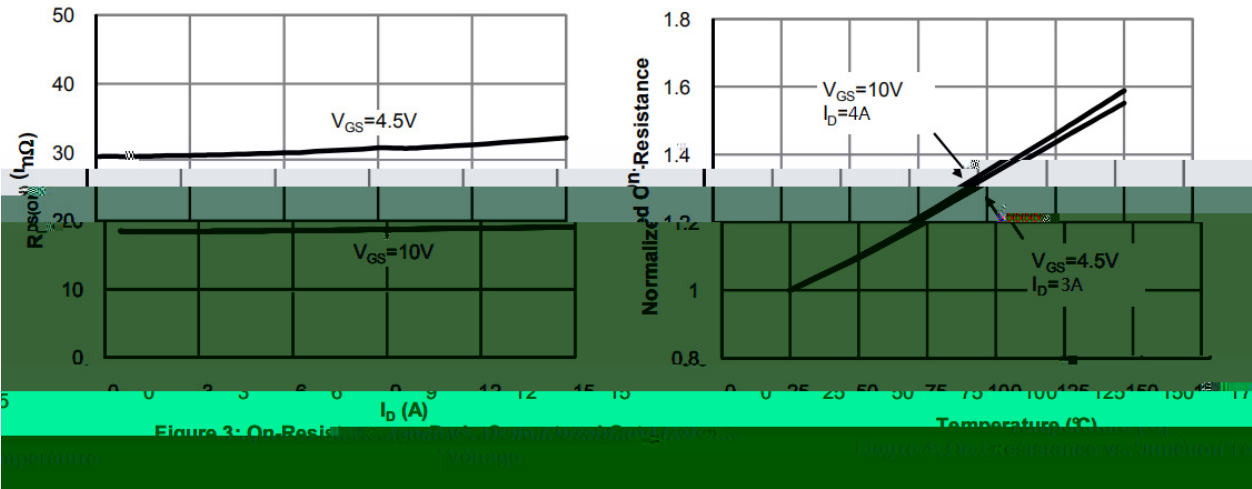
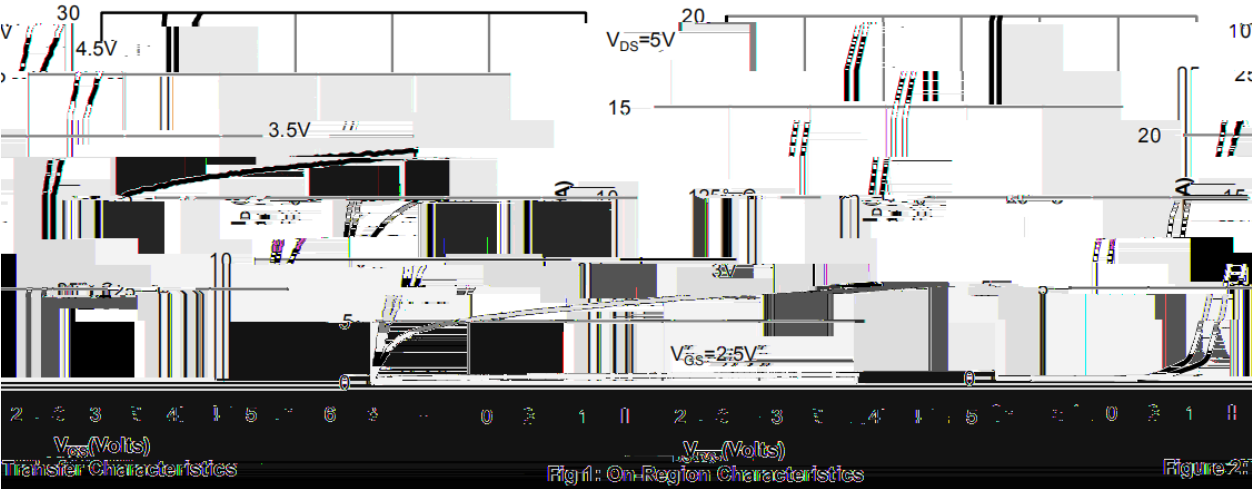
/ Marking

See Marking Instructions.

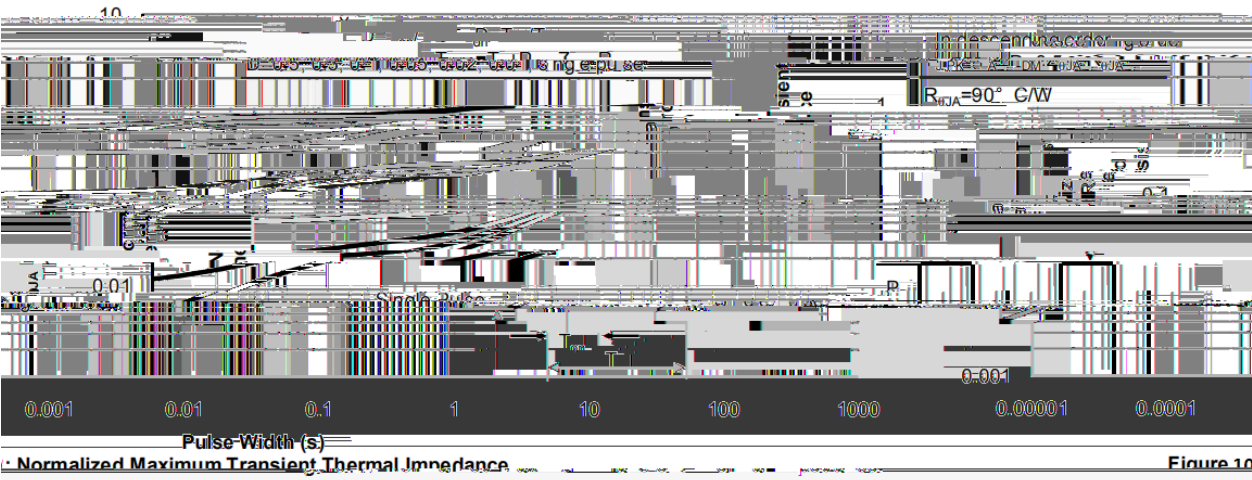
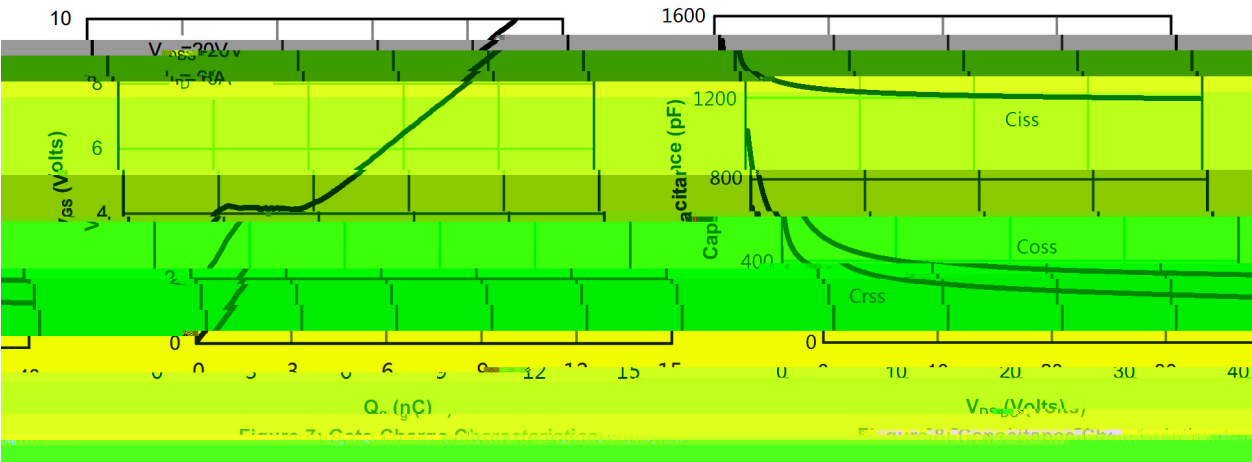

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_g(10V)$	$V_{GS}=10V \quad V_{DS}=20V$ $I_D=6A$		15.4		nC
Total Gate Charge	$Q_g(4.5V)$			7.0		
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			2.9		

Electrical Characteristic Curve



/ Electrical Characteristic Curve





/ Package Dimensions

, M y f / Marking Instructions

BR
200N04D

^a ¢ y
BR y , [W A
4 * y ° Z W A
y Ÿ D Z W A k Š Ÿ D Z J

Note:
BR: Company Code.
200N04D y Product Type.
***: Lot No. Code, code change with Lot No

šWD t...•Žč (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

^ačy

10• Ä½ “† 150 ½180 - kž • 60 ½90sec;

20• Q> “† 245 r5 - kž • 4 Ò 5 r0.5sec;

30•D N ò i Ò 0 ,† 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3.